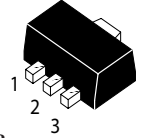


PNP Plastic-Encapsulate Transistor

 Lead(Pb)-Free

SOT-89


1. BASE
2. COLLECTOR
3. EMITTER

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	-80	V _{dc}
Collector-Base Voltage	V _{CBO}	-80	V _{dc}
Emitter-Base Voltage	V _{EBO}	-5.0	V _{dc}
Collector Current	I _C	1.0	A _{dc} (DC)
	I _{CP}	2.0	A _{dc} (Pulse)
Collector Power Dissipation	P _C	0.5	W
Junction Temperature, Storage Temperature	T _j , T _{stg}	150, -55 to +150	°C

Device Marking

2SB1260=ZL

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage (I _C = -1.0 mA _{dc} , I _B =0)	V _{(BR)CEO}	-80	-	V _{dc}
Collector-Base Breakdown Voltage (I _C = -50 μA _{dc} , I _E =0)	V _{(BR)CBO}	-80	-	V _{dc}
Emitter-Base Breakdown Voltage (I _E = -50 μA _{dc} , I _C =0)	V _{(BR)EBO}	-5.0	-	V _{dc}
Collector Cutoff Current (V _{CB} = -60 V _{dc} , I _E =0)	I _{CBO}	-	-1	μA _{dc}
Emitter Cutoff Current (V _{EB} =-4.0 V _{dc} , I _C =0)	I _{EBO}	-	-1	μA _{dc}

1.FR-5=1.0 x 0.75 x 0.062 in.

2SB1260



ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted) (Continued)

Characteristics	Symbol	Min	Typ	Max	Unit
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ON CHARACTERISTICS

DC Current Gain ($I_C=-0.1\text{ A dc}, V_{CE}=-3.0\text{ V dc}$)	h_{FE}	82	-	390	-
Collector-Emitter Saturation Voltage ($I_C=-500\text{ mA dc}, I_B=-50\text{ mA dc}$)	$V_{CE(sat)}$	-	-	-0.4	Vdc
Transition Frequency ($I_C=-50\text{ mA dc}, V_{CE}=-5.0\text{ V dc}, f=30\text{ MHz}$)	f_T	80	-	-	MHz

CLASSIFICATION OF h_{FE}

Item	P	Q	R
Range	82-180	120-270	180-390

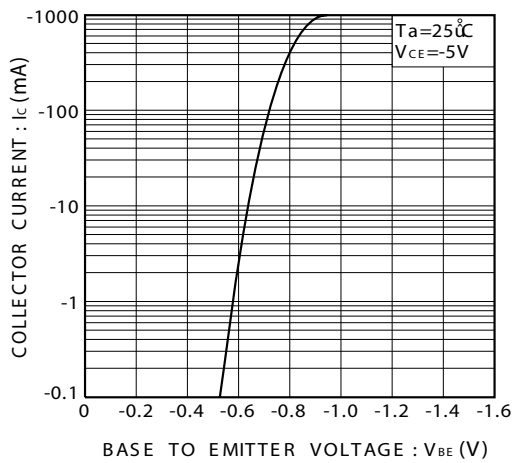


FIG.1 Grounded Emitter Propagation Characteristics

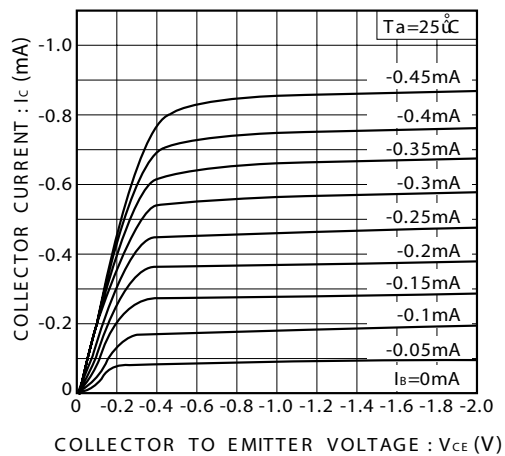


FIG.2 Grounded Emitter Output Characteristics

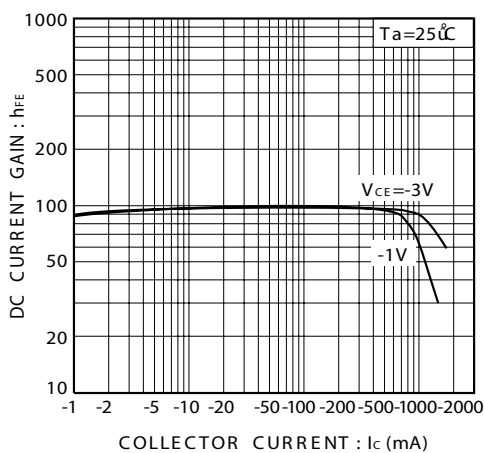


FIG.3 DC Current Gain vs. Collector Current

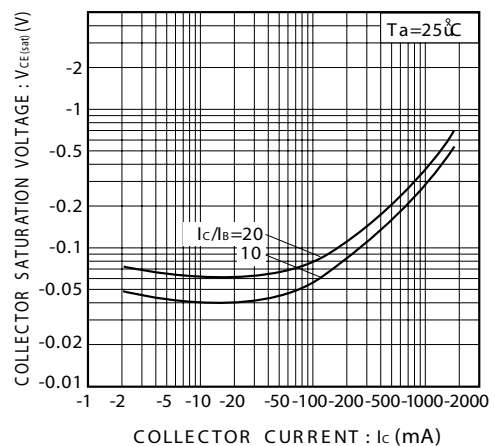


FIG.4 Collector-Emitter Saturation Voltage vs. Collector Current

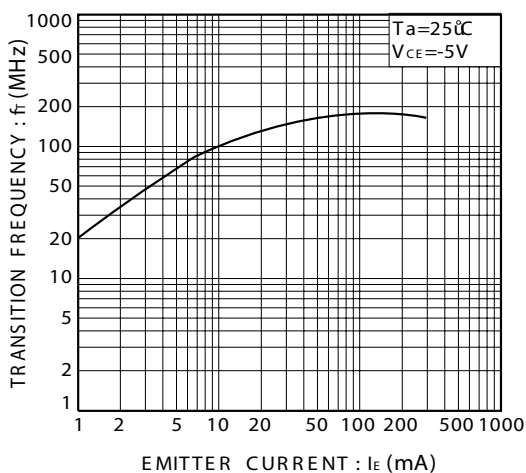


FIG.5 Gain Bandwidth Product vs. Emitter Current

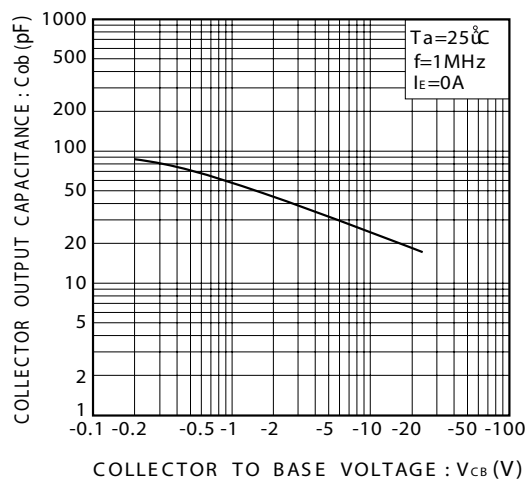


FIG.6 Collector Output Capacitance vs. Collector-Base Voltage

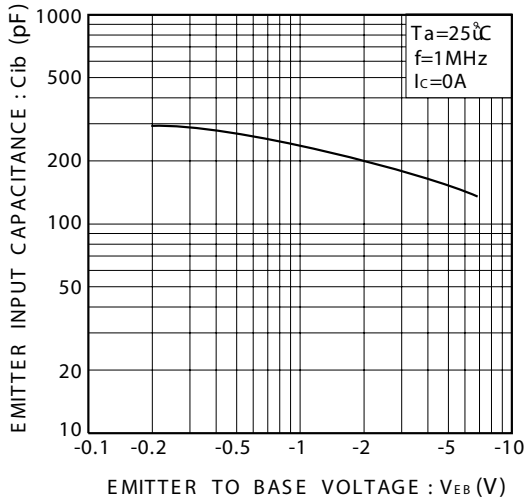


FIG. 7 Emitter Input Capacitance vs. Emitter-Base Voltage

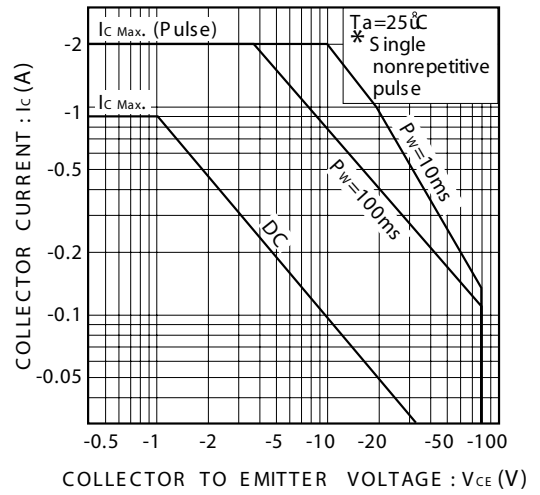
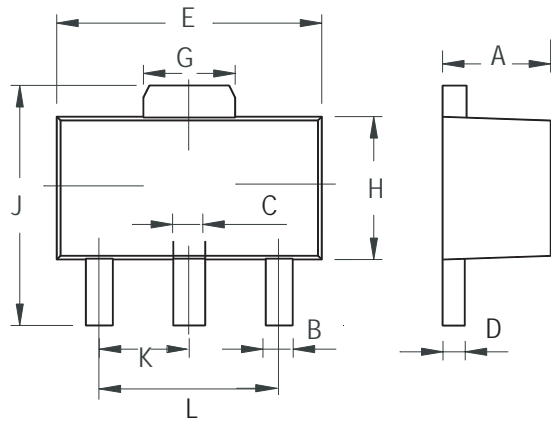


FIG. 8 Safe Operating Area

SOT-89 Outline Dimensions

unit:mm



SOT-89		
Dim	Min	Max
A	1.400	1.600
B	0.320	0.520
C	0.360	0.560
D	0.350	0.440
E	4.400	4.600
G	1.400	1.800
H	2.300	2.600
J	3.940	4.250
K	1.500TYP	
L	2.900	3.100